Silicon NPN Power Transistors 2SD531

DESCRIPTION

·With TO-220C package
·High current capability

APPLICATIONS

·For audio frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

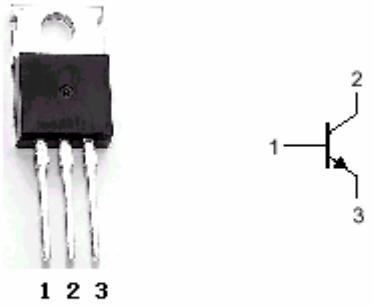

Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Tc=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	100	V
V_{CEO}	Collector-emitter voltage	Open base	90	V
V_{EBO}	Emitter-base voltage	Open collector	8	V
I_C	Collector current		5	A
P_C	Collector power dissipation	T_C=25□	43	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=50mA; R_{BE}=∞	90			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=5mA; I_E=0	100			V
$V_{(BR)EBO}$	Emitter-base breakdown votage	I_E=5mA; I_C=0	8			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=4A;I_B=0.4 A			2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=100V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=0.1A ; V_{CE}=2V	60			

PACKAGE OUTLINE

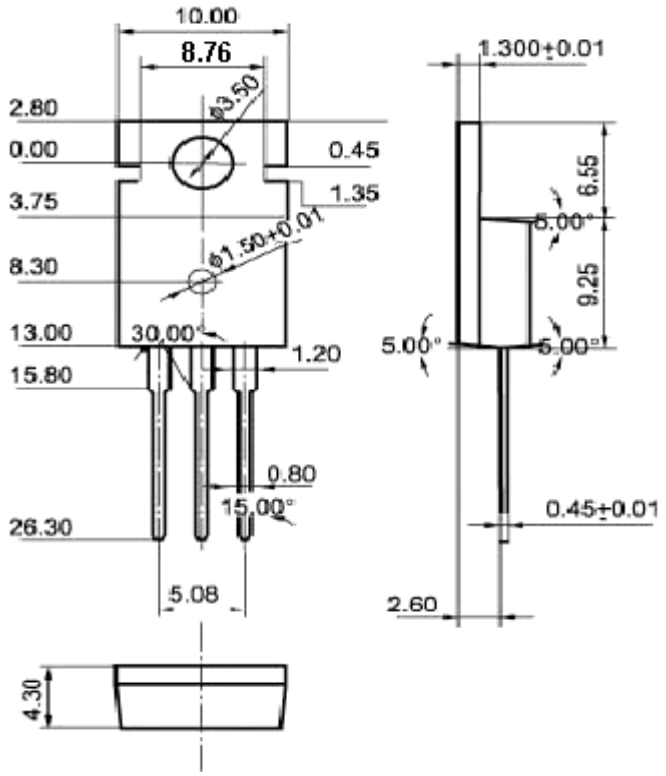

Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)